

## PATENT

Atty. Dkt. No. APPM/005750/CPIA/B/PJS

**IN THE CLAIMS:**

Please amend the claims as follows.

1. (Currently Amended) A cleaning method for a vapor phase deposition apparatus for forming film ~~onto~~ on a substrate ~~by introducing film forming gas into a chamber via a shower head,~~ comprising:

introducing a film forming gas into a chamber via a shower head;

forming a film on the substrate with the shower head at a first temperature;

activating a cleaning gas including a compound containing fluorine atoms by exposure to microwaves, ~~and then~~ ;

introducing the cleaning gas into ~~a~~ the chamber;

raising a the temperature of a the shower head to a second temperature greater than the first temperature ~~that used when forming a film on a substrate;~~ and then

removing a deposit comprising tungsten and silicon.

2. (Previously Presented) A cleaning method for a vapor phase deposition apparatus according to claim 1, wherein raising the temperature of the shower head comprises restricting a supply of a cooling medium to the shower head.

3. (Previously Presented) A cleaning method for a vapor phase deposition apparatus according to claim 2, wherein raising the temperature of the shower head further comprises heating the shower head by a heater.

4. (Previously Presented) A cleaning method for a vapor phase deposition apparatus according to claim 1, wherein raising the temperature of the shower head comprises heating the shower head by a heater.

5. (Previously Presented) A cleaning method for a vapor phase deposition apparatus according to claim 1, wherein the temperature of the shower head is raised to about 50°C or above.

6. (Currently Amended) A cleaning method for a vapor phase deposition apparatus ~~according to claim 1,~~ for forming film on a substrate, comprising:

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introducing a film forming gas into a chamber via a shower head wherein the film forming gas ~~includes gas consisting of~~ comprises a compound containing tungsten atoms[~~(,)~~];

forming a film on the substrate with the shower head at a first temperature;

activating a cleaning gas including a compound containing fluorine atoms by exposure to microwaves;

introducing the cleaning gas into a chamber;

raising the temperature of the shower head to a second temperature greater than the first temperature, and wherein the temperature of the shower head is raised to about 70°C or above; and then

removing a deposit comprising tungsten and silicon.

7-13. (Canceled)